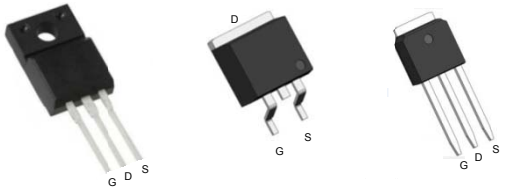
600V 1.0Ω Super Junction Power MOSFET

Description

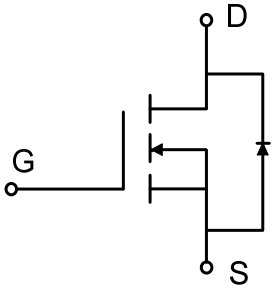
WMOS^{TM} C2 is Wayon's 2nd generation super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS^{TM} C2 is suitable for applications which require superior power density and outstanding efficiency.



Features

- V_{DS} =650V @ $T_{j,max}$
- Typ. $R_{DS(on)}$ =1.0Ω
- 100% UIS tested
- Pb-free plating, Halogen free

RoHS compliant



Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server

Absolute Maximum Ratings

Parameter	Symbol	WMH/WMM/WMO/WMP/WMG	WML	Unit
Drain-source voltage	V_{DSS}	600		V
Continuous drain current[1] (T_C = 25°C)	I_D	5		A
(T_C = 100°C)		3		A
Pulsed drain current[2]	I_{DM}	9		A
Gate-source voltage	V_{GS}	±30		V
Avalanche energy, single pulse[3]	E_{AS}	15		mJ
Avalanche energy, repetitive[2]	E_{AR}	0.1		mJ
Avalanche current, repetitive[2]	I_{AR}	0.7		A
Power dissipation (T_C = 25°C)	P_D	42	23	W
- Derate above 25°C		0.34	0.18	W/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		°C
Continuous diode forward current	I_S	5		A
Diode pulse current	$I_{S,pulse}$	9		A

Thermal Characteristics

Parameter	Symbol	WMH/WMM/WMO/WMP/WMG	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	3	5.4	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	°C/W

Electrical Characteristics T_c = 25°C, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25mA	2.5	3.3	4.5	V
Drain cut-off current	I_{DSS}	V_{DS}=600 V, V_{GS}=0 V,				μA
		T_j = 25°C	-	-	1	
		T_j = 125°C	-	10	-	
Gate leakage current, forward	I_{GSSF}	V_{GS}=30 V, V_{DS}=0 V	-	-	100	nA
Gate leakage current, reverse	I_{GSSR}	V_{GS}=-30 V, V_{DS}=0 V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=2A	-			
		T_j = 25°C	-	1.0	1.14	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS}= 25 V, V_{GS}= 0 V,	-	270	-	
Output capacitance	C_{oss}	f = 1 MHz	-	200	-	pF
Reverse transfer capacitance	C_{rss}		-	2	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 300V, I_D = 2A	-	5	-	
Rise time	t_r	R_G = 25Ω, V_{GS}=10V	-	16	-	ns
Turn-off delay time	$t_{d(off)}$		-	24	-	
Fall time	t_f		-	12	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480 V, I_D=2A,	-	1.6	-	
Gate to drain charge	Q_{gd}	V_{GS}=0 to 10 V	-	1.7	-	nC
Gate charge total	Q_g		-	5.8	-	
Gate plateau voltage	$V_{plateau}$		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=2A	-	-	1.2	V
Reverse recovery time	t_{rr}	V_R=50 V, I_F=2A,	-	163	-	ns
Reverse recovery charge	Q_{rr}	dI_F/dt=100 A/μs	-	0.84	-	μC
Peak reverse recovery current	I_{rrm}		-	10.3	-	A

Notes:

1. Limited by $T_{j\,max}$. Maximum duty cycle D=0.5.

2. Repetitive rating: pulse width limited by maximum junction temperature

3. I_{AS} = 0.7A, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C

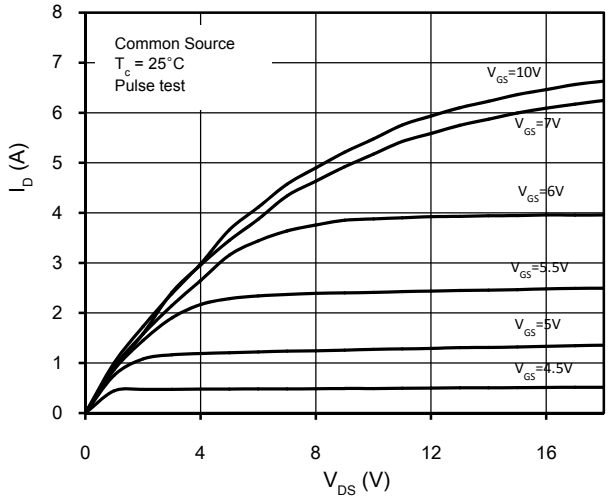


Figure 1.On-Region Characteristics

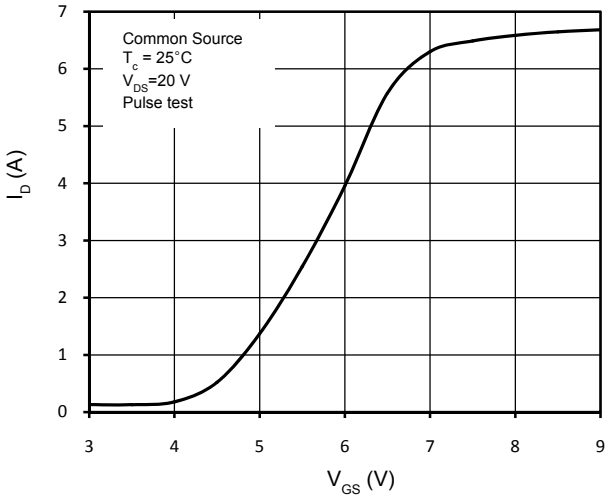


Figure 2. Transfer Characteristics

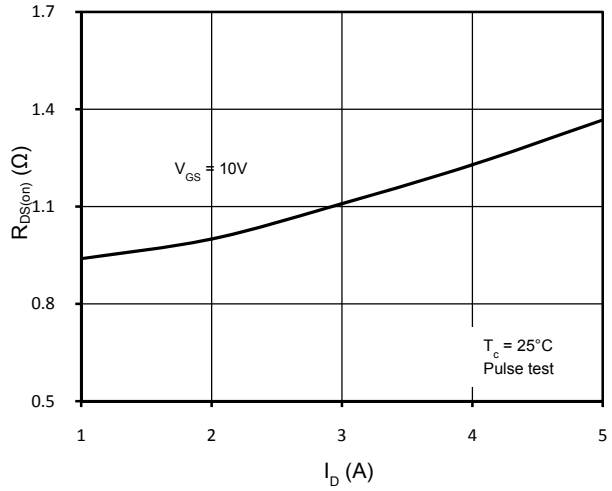


Figure 3. Static Drain-Source On Resistance

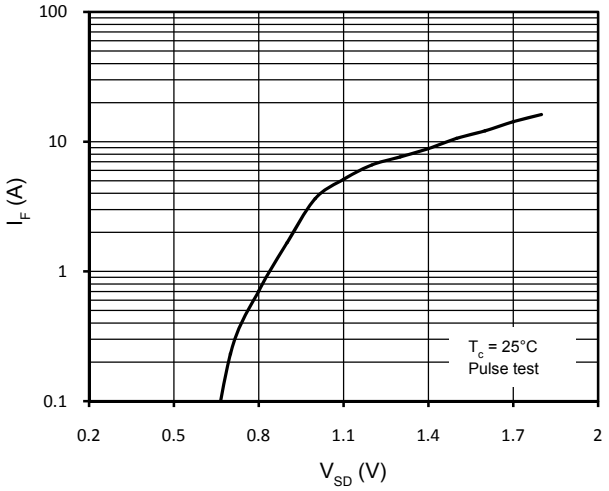


Figure 4. Body- Diode Forward Characteristics

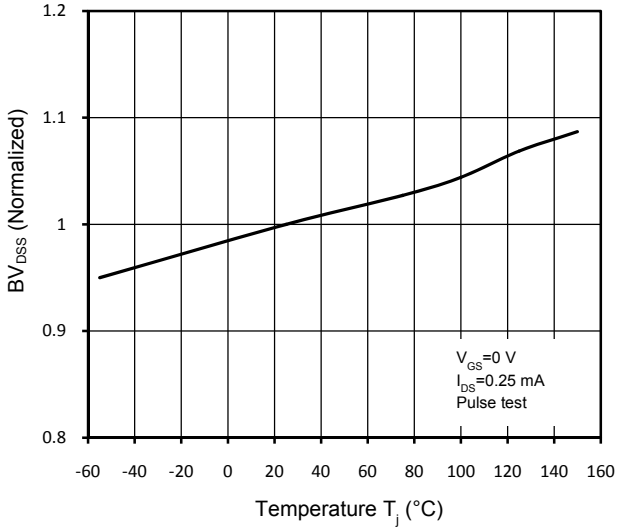


Figure 5. Normalized BV_{DSS} vs. Temperature

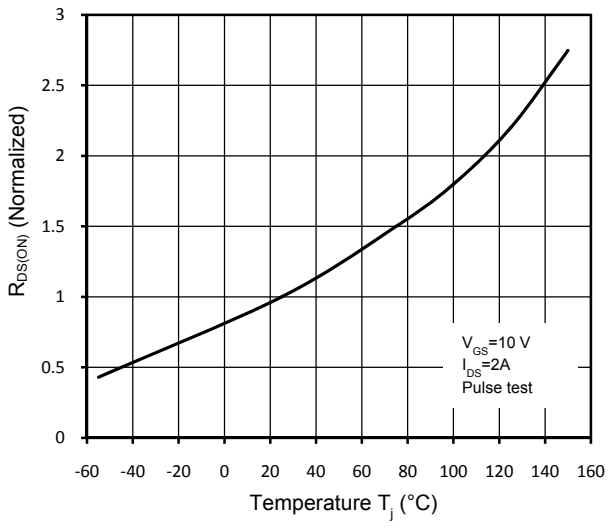


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

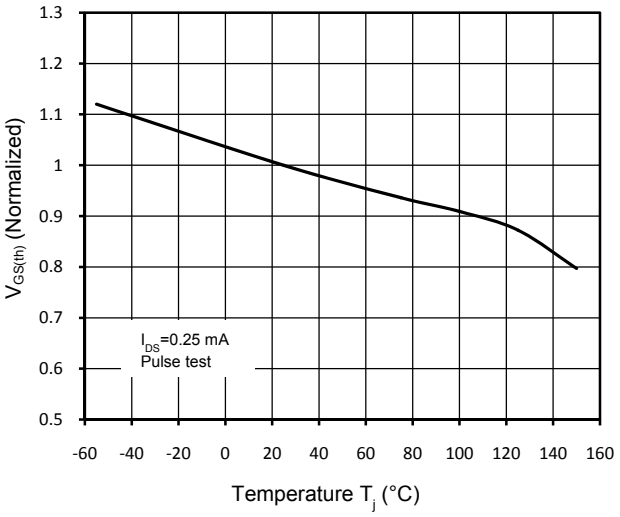


Figure 7. Threshold Voltage vs. Temperature

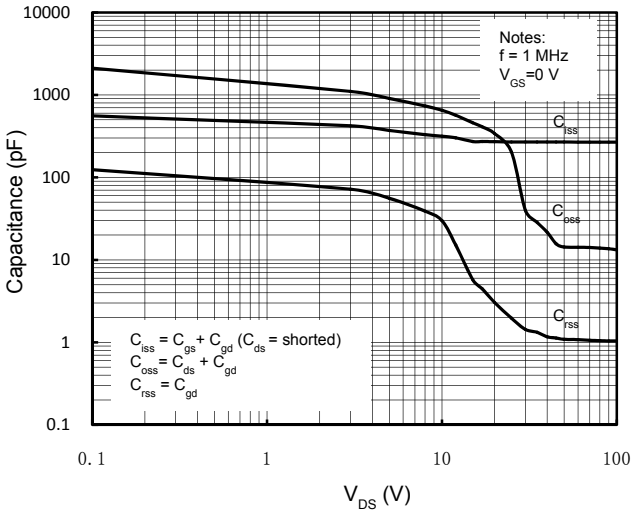


Figure 8. Capacitance Characteristics

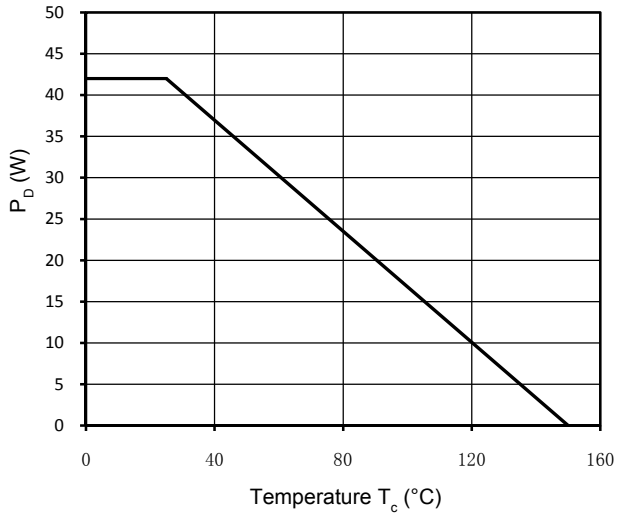


Figure 9. Power Dissipation

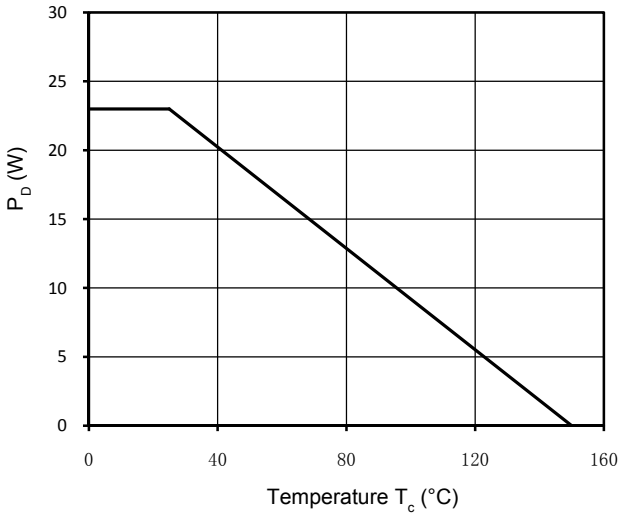


Figure 10. Power Dissipation (TO-220F)

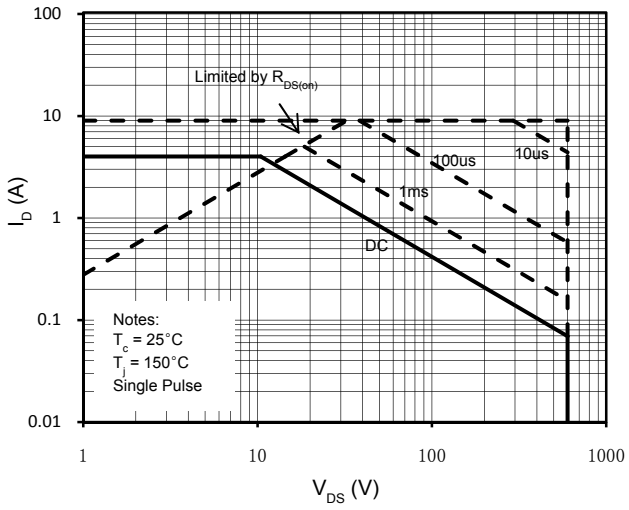


Figure 11. Maximum Safe Operating Area

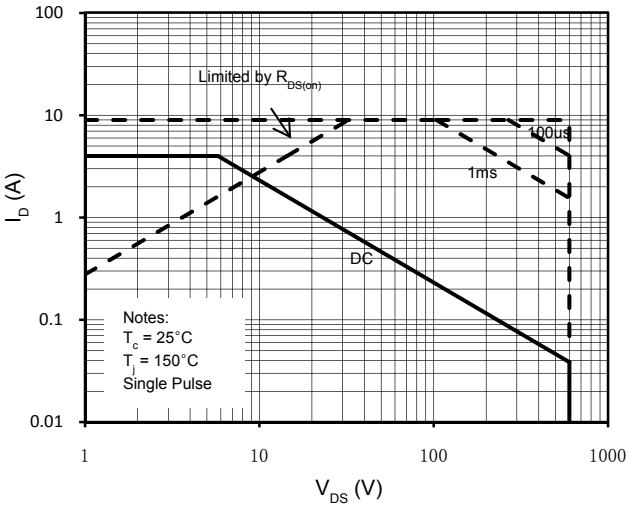


Figure 12. Maximum Safe Operating Area(TO-220F)

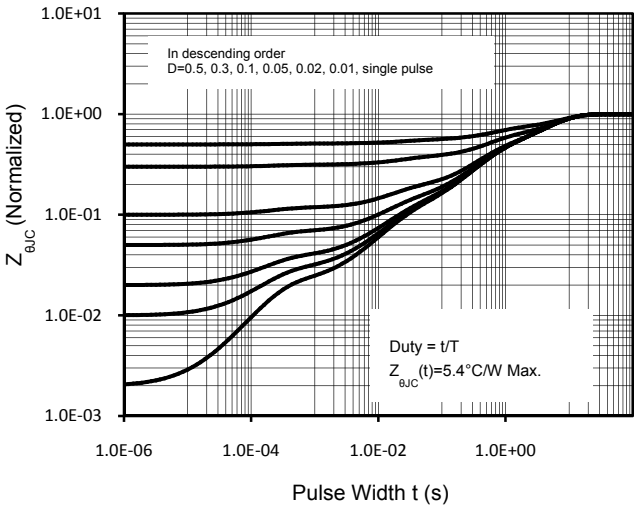


Figure 13. Transient Thermal Response Curve (TO-220F)

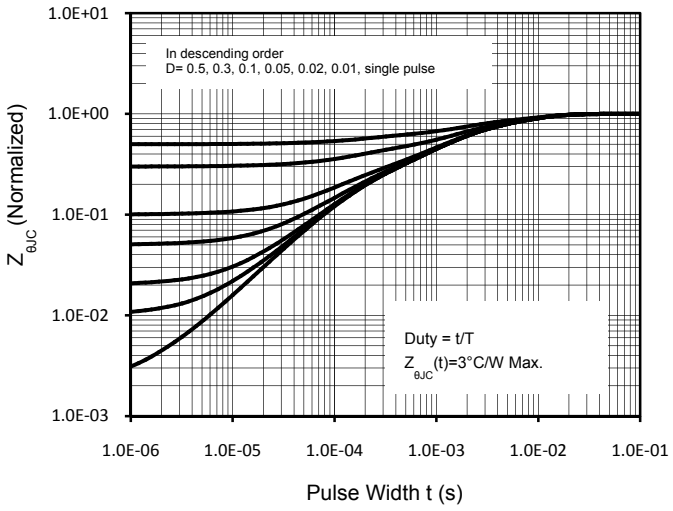


Figure 14. Transient Thermal Response Curve

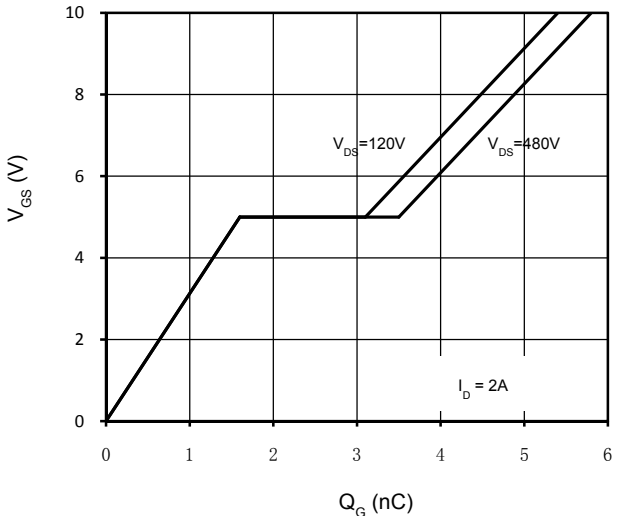
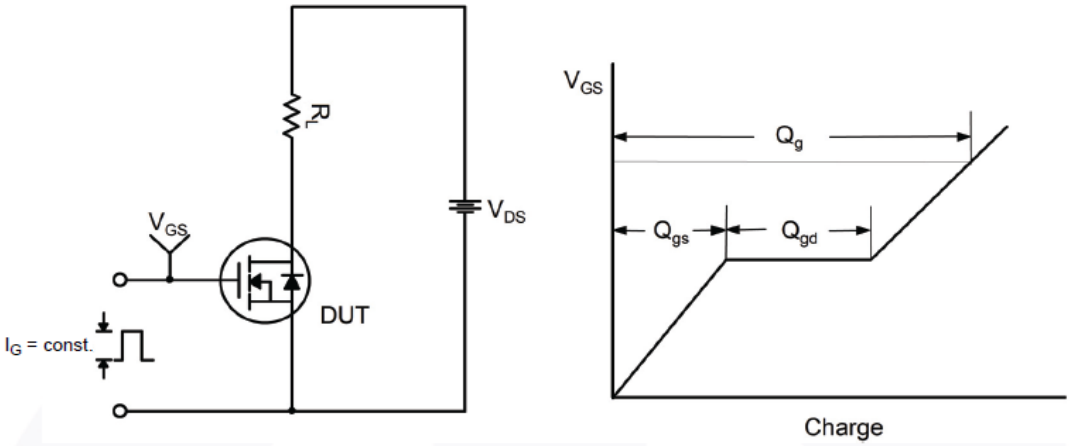
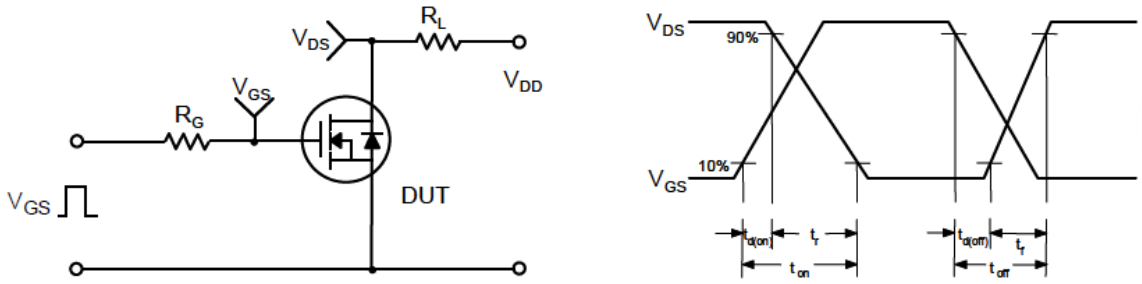


Figure 15. Gate Charge Characteristics

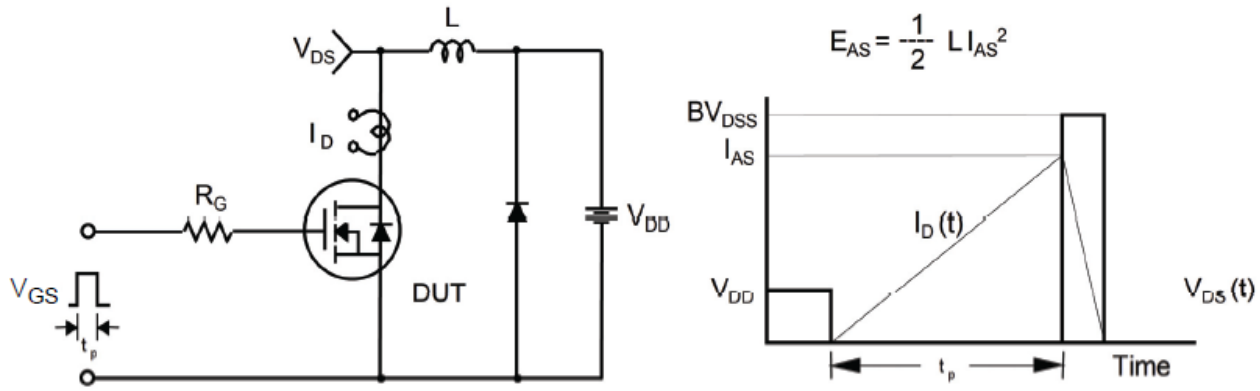
Gate Charge Test Circuit & Waveform



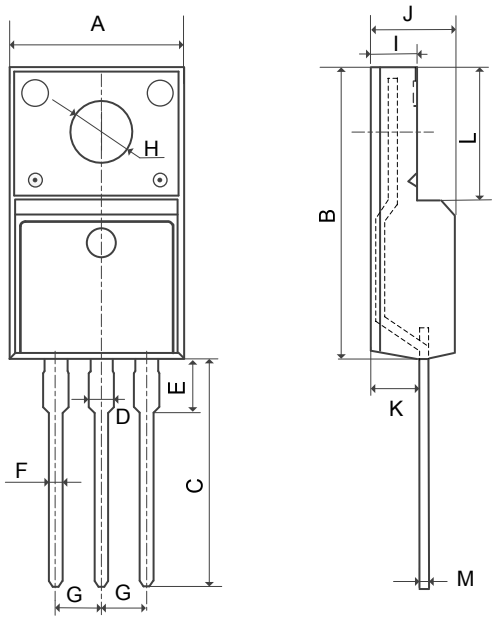
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



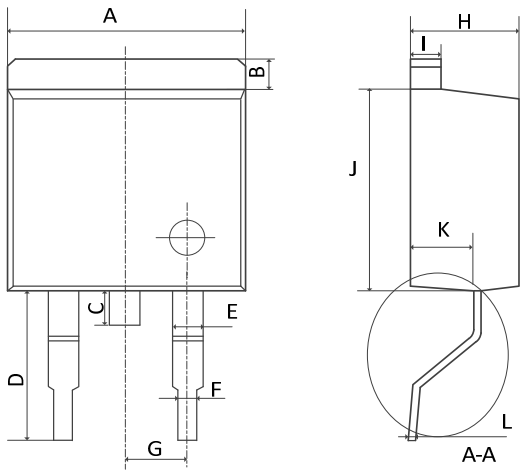
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.67	16.07
C	12.70	13.30
D	1.12	1.32
E	1.85	2.15
F	0.59	0.79
G	2.39	2.69
H	3.08	3.29
I	2.34	2.74
J	4.50	4.90
K	2.61	2.91
L	6.50	6.90
M	0.40	0.60

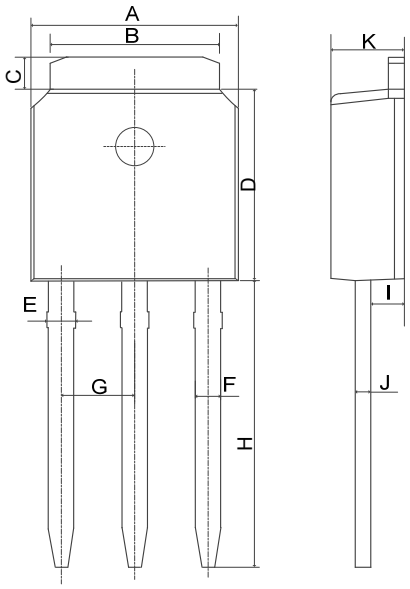
Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	10.00	10.40
B	1.11	1.41
C	1.25	1.55
D	5.10	5.50
E	1.12	1.42
F	0.71	0.92
G	2.39	2.69
H	4.49	4.89
I	1.17	1.37
J	8.45	8.85
K	2.54	2.84
L	0.28	0.49

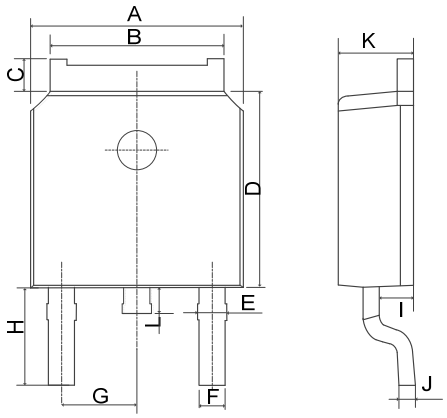
Mechanical Dimensions for TO-251



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.46
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	9.00	9.65
I	0.90	1.17
J	0.40	0.61
K	2.10	2.50

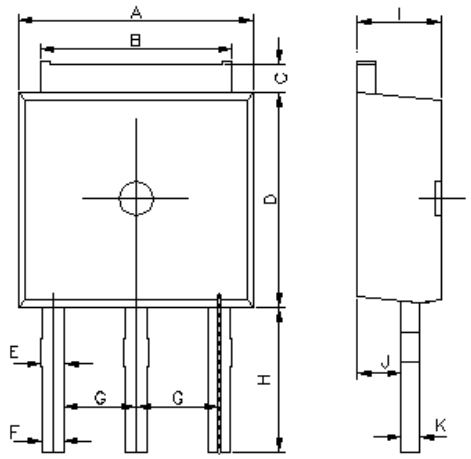
Mechanical Dimensions for TO-252



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

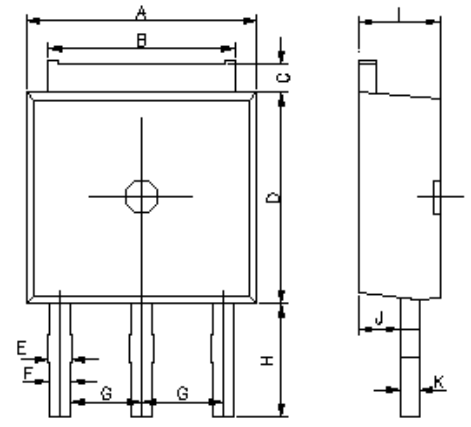
Mechanical Dimensions for TO-251S3



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.15	5.48
C	0.71	1.02
D	5.95	6.35
E	0.70	1.00
F	0.70	0.90
G	2.13	2.44
H	3.20	3.80
I	2.10	2.50
J	0.85	1.15
K	0.40	0.61

Mechanical Dimensions for TO-251S2



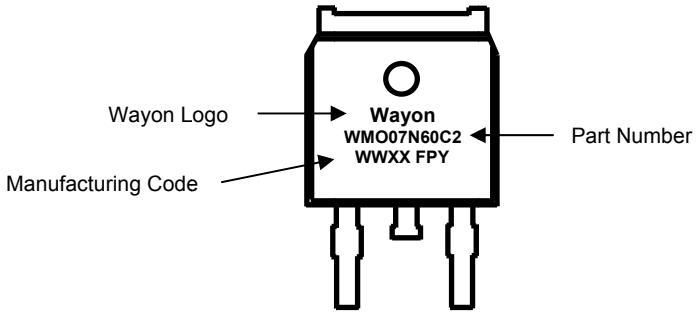
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.15	5.48
C	0.71	1.02
D	5.95	6.35
E	0.70	1.00
F	0.70	0.90
G	2.13	2.44
H	2.20	2.80
I	2.10	2.50
J	0.85	1.15
K	0.40	0.61

Ordering Information

Part	Package	Marking	Packing method
WML07N60C2	TO-220F	WML07N60C2	Tube
WMM07N60C2	TO-263	WMM07N60C2	Tape and Reel
WMO07N60C2	TO-252	WMO07N60C2	Tape and Reel
WMP07N60C2	TO-251	WMP07N60C2	Tube
WMG07N60C2	TO-251S3	WMG07N60C2	Tube
WMH07N60C2	TO-251S2	WMH07N60C2	Tube

Marking Information



Contact Information

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WAYON website: **http://www.way-on.com**
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